

L Number	Hits	Search Text	DB	Time stamp
-	1	("6451512").PN.	USPAT; US-PGPUB	2003/06/28 12:30
-	3	((("5563238") or ("3811931") or ("3676401"))).PN.	USPAT; US-PGPUB	2003/06/28 15:11
-	1862	(resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/28 15:29
-	1101	((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/28 15:46
-	397	((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/06/28 15:47
-	42	((((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (430/311,319,327-329).ccls.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:12

-	355	(((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) not (((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (430/311,319,327-329).ccls.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:14
-	0	((light) near3 (degrad\$4) near3 (prim\$3 or adhes\$7) same (resist or photoresist)) not (((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) not (((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (430/311,319,327-329).ccls.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:15
-	0	((light) near3 (degrad\$4) near3 (prim\$3 or adhes\$7) same (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:15
-	12	((light) near3 (degrad\$4) near3 (prim\$3 or adhes\$7) and (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:16
-	0	((light) near3 (degrad\$4) with (primer or priming) same (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:17

-	88	((bilayer or bi adj layer) same positive near2 (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/07/16 16:27
-	74	((bilayer or bi adj layer) same positive near2 (resist or photoresist))) and (thick or thickness) same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:17
-	2	((hexamethyldisilazane or HMDS) near5 decompos\$4) same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:18
-	12	((hexamethyldisilazane or HMDS) near5 (light or uv)) same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:18
-	92	(134/1.3).ccls. and (light or uv) same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2003/07/18 15:34
-	6	((134/1.3).ccls. and (light or uv) same (resist or photoresist)) and (hexamethyldisilazane or HMDS)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:19
-	17	((hexamethyldisilazane or HMDS) near5 (light or uv or ultraviolet)) same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:19
-	16	(light or uv or ultraviolet) same ((bond\$3 or coupl\$3) near2 (strength or energy)) same ((silicon or Si) near5 (oxygen))	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:20
-	19	(light or uv or ultraviolet) same ((bond\$3 or coupl\$3) near2 (strength or energy)) same ("Si--O" or "O--Si")	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:20
-	47	((((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (430/311,319,327-329).ccls.	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:13

-	405	(((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) not (((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (430/311,319,327-329).ccls.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:14
-	0	((light) near3 (degrad\$4) near3 (prim\$3 or adhes\$7) same (resist or photoresist)) not (((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) not (((resist or photoresist or photopolymer\$7) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7) with (lactic or ketone or organometal\$3 or metal adj salt or siloxane or silane or hexamethyldisilazane or HMDS)) and (semiconduct\$3 or semi adj conduct\$3 or wafer or silicon or "Si") same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (degrad\$4 or decompos\$5 or break\$3 or downgrad\$4 or deteriorat\$4 or disintegrat\$4 or decay\$3 or dissolv\$4 or fragment\$4) same (coupl\$3 or bond\$3 or prim\$3 or adhes\$7)) and (430/311,319,327-329).ccls.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:15
-	0	((light) near3 (degrad\$4) near3 (prim\$3 or adhes\$7) same (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:16
-	13	((light) near3 (degrad\$4) near3 (prim\$3 or adhes\$7) and (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:16
-	0	((light) near3 (degrad\$4) with (primer or priming) same (resist or photoresist))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/01/17 18:17

-	83	((bilayer or bi adj layer) same positive near2 (resist or photoresist))) and (thick or thickness) same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:17
-	2	((hexamethyldisilazane or HMDS) near5 decompos\$4) same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:18
-	15	((hexamethyldisilazane or HMDS) near5 (light or uv)) same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:18
-	6	((134/1.3).ccls. and (light or uv) same (resist or photoresist)) and (hexamethyldisilazane or HMDS)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:19
-	20	((hexamethyldisilazane or HMDS) near5 (light or uv or ultraviolet)) same (resist or photoresist)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:20
-	19	(light or uv or ultraviolet) same ((bond\$3 or coupl\$3) near2 (strength or energy)) same ((silicon or Si) near5 (oxygen))	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:20
-	20	(light or uv or ultraviolet) same ((bond\$3 or coupl\$3) near2 (strength or energy)) same ("Si--O" or "O--Si")	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/17 18:20
-	20	(polydimethylglutarimide or polymethylglutarimide or polyglutarimide or PMGI) same (polar\$3 or nonpolar\$3 or hydrophilic or hydrophobic)	USPAT; US-PGPUB; EPO; JPO; IBM TDB	2004/01/20 19:50